



Description

The HXY3030BGD uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 30V$ $I_D = 30A$

$R_{DS(ON)} < 13m\Omega$ @ $V_{GS}=10V$

$V_{DS} = -30V$ $I_D = -30A$

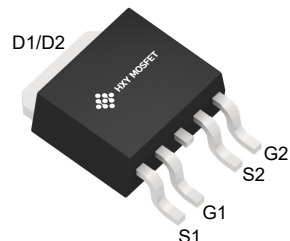
$R_{DS(ON)} < 25m\Omega$ @ $V_{GS}=-10V$

Application

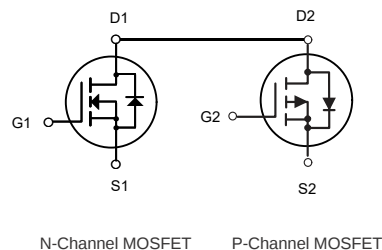
Wireless charging

Boost driver

Brushless motor



TO-252-4L



N-Channel MOSFET

P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HXY3030BGD	TO-252-4L	3030 XXXX	2500

Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating		Units
		N-Channel	P-Channel	
V_{DS}	Drain-Source Voltage	30	-30	V
V_{GS}	Gate-Source Voltage	± 20	± 20	V
$I_{D@T_c=25^\circ C}$	Continuous Drain Current, V_{GS} @ 10V ¹	30	-30	A
$I_{D@T_c=100^\circ C}$	Continuous Drain Current, V_{GS} @ 10V ¹	15	-16	A
IDM	Pulsed Drain Current ²	46	-40	A
EAS	Single Pulse Avalanche Energy ³	28	66	mJ
$P_D@T_A=25^\circ C$	Total Power Dissipation ⁴	15	21.3	W
TSTG	Storage Temperature Range	-55 to 150	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	48		$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	5		$^\circ C/W$



N-Channel Electrical Characteristics($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.8	2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance note3	V _{GS} =10V, I _D =10A	-	9.5	13	mΩ
		V _{GS} =4.5V, I _D =5A	-	16	22.5	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1.0MHz	-	633	-	pF
C _{oss}	Output Capacitance		-	120	-	pF
C _{rss}	Reverse Transfer Capacitance		-	99	-	pF
Q _g	Total Gate Charge	V _{DS} =15V, I _D =10A, V _{GS} =10V	-	15	-	nC
Q _{gs}	Gate-Source Charge		-	4.7	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	3.6	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =30V,I _D =18A, R _{GEN} =3Ω, V _{GS} =10V	-	5	-	ns
t _r	Turn-on Rise Time		-	8	-	ns
t _{d(off)}	Turn-off Delay Time		-	21	-	ns
t _f	Turn-off Fall Time		-	7	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _s	Maximum Continuous Drain to Source Diode Forward Current		-	-	30	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	72	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =18A	-	-	1.2	V
t _{rr}	Body Diode Reverse Recovery Time	I _F =18A,dI/dt=100A/μs	-	7	-	ns
Q _{rr}	Body Diode Reverse Recovery Charge		-	5.9	-	nC

Note :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
2. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. The EAS data shows Max. rating . The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=20A$
4. The power dissipation is limited by 150°C junction temperature
5. The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



P-Channel Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = -250μA	-30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -30V, V _{GS} =0V	-	-	-1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D = -250μA	-1.0	-1.8	-2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance note3	V _{GS} = -10V, I _D = -10A	-	20	25	mΩ
		V _{GS} = -4.5V, I _D = -5A	-	31	40	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = -15V, V _{GS} =0V, f=1.0MHz	-	1240	-	pF
C _{oss}	Output Capacitance		-	151	-	pF
C _{rss}	Reverse Transfer Capacitance		-	138	-	pF
Q _g	Total Gate Charge	V _{DS} = -15V, I _D = -6A, V _{GS} = -10V	-	24	-	nC
Q _{gs}	Gate-Source Charge		-	3.7	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	4.8	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} = -15V, I _D = -10A, V _{GS} = -10V, R _{GEN} =3Ω	-	11	-	ns
t _r	Turn-on Rise Time		-	5.5	-	ns
t _{d(off)}	Turn-off Delay Time		-	3.5	-	ns
t _f	Turn-off Fall Time		-	4.6	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-30	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-40	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S = -10A	-	-	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: $T_J=25^{\circ}\text{C}$, $V_{DD}=-15V$, $V_G=-10V$, $R_G=25\Omega$, $L=0.1mH$, $I_{AS}=-27A$

3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$



N-Channel Typical Characteristics

Figure1: Output Characteristics

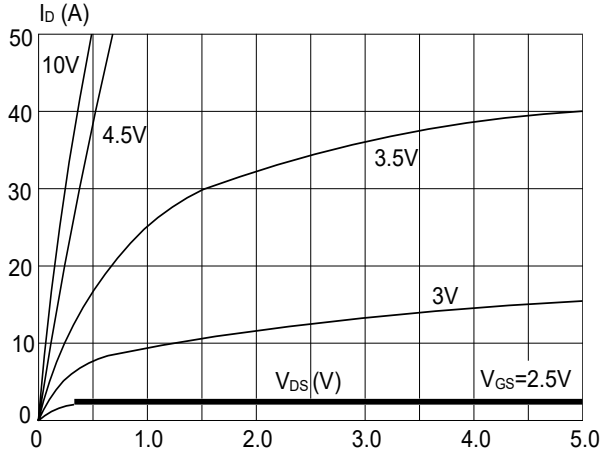


Figure 2: Typical Transfer Characteristics

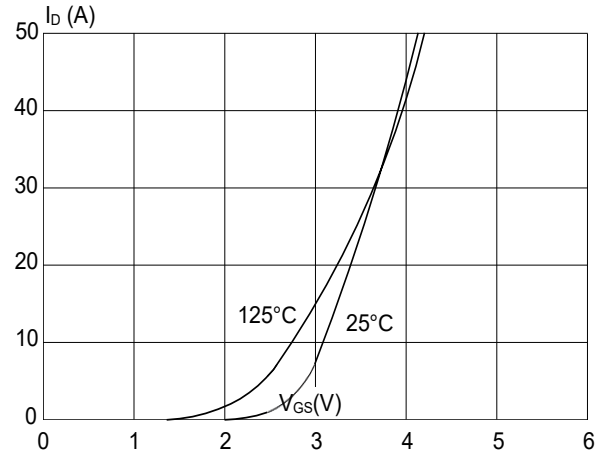


Figure 3: On-resistance vs. Drain Current

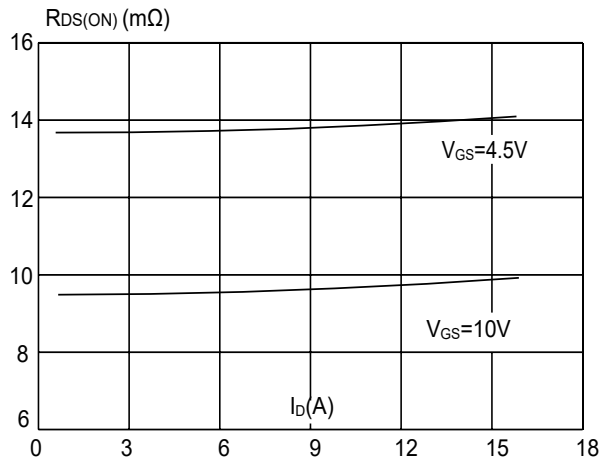


Figure 4: Body Diode Characteristics

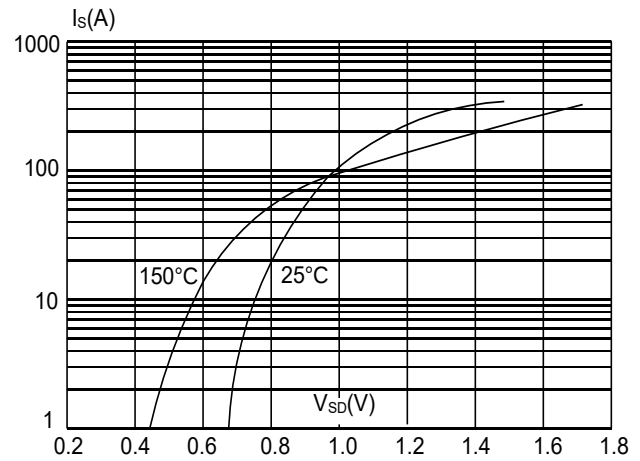


Figure 5: Gate Charge Characteristics

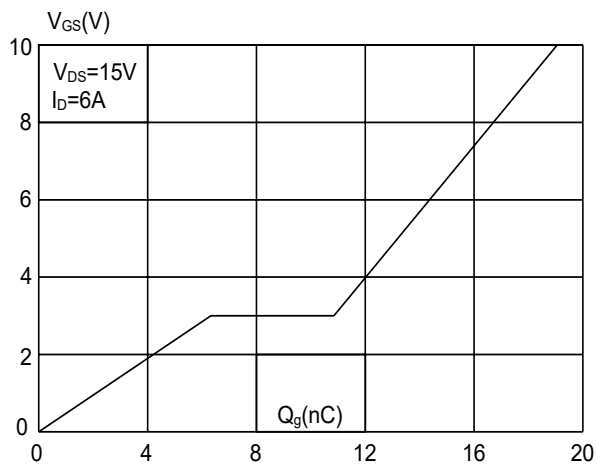


Figure 6: Capacitance Characteristics

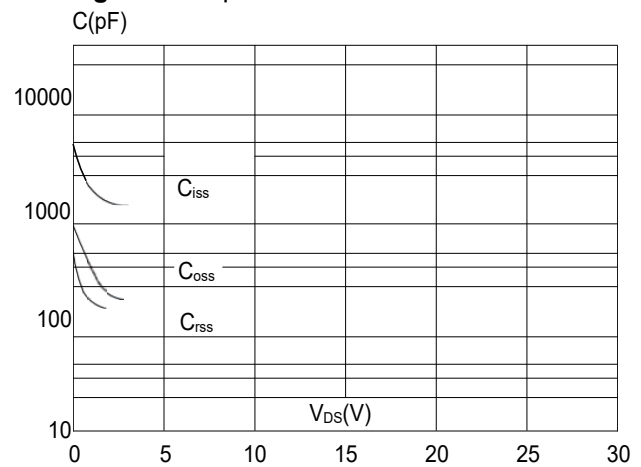




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

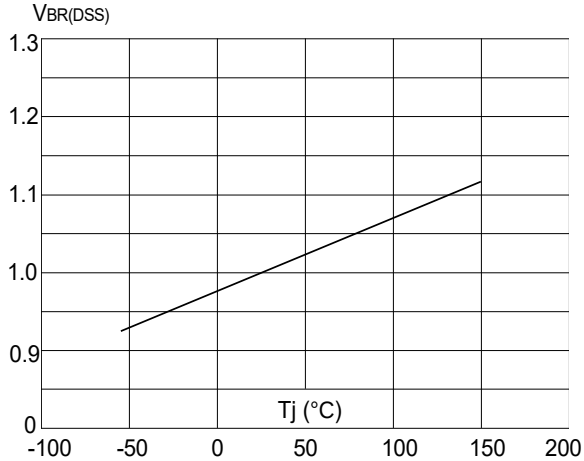


Figure 8: Normalized on Resistance vs. Junction Temperature

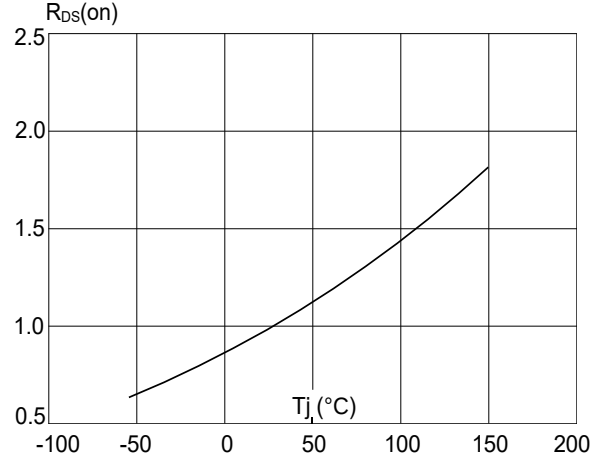


Figure 9: Maximum Safe Operating Area

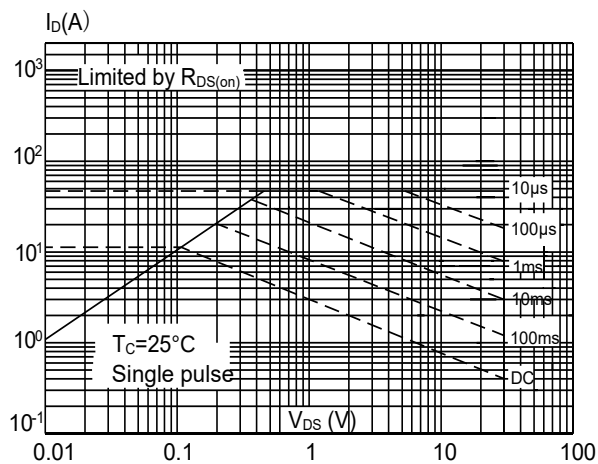


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

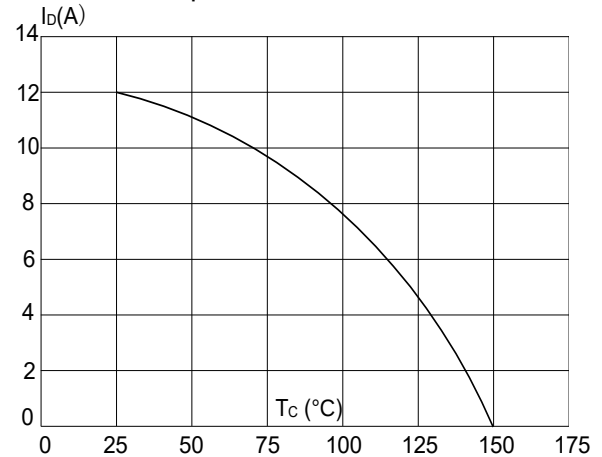
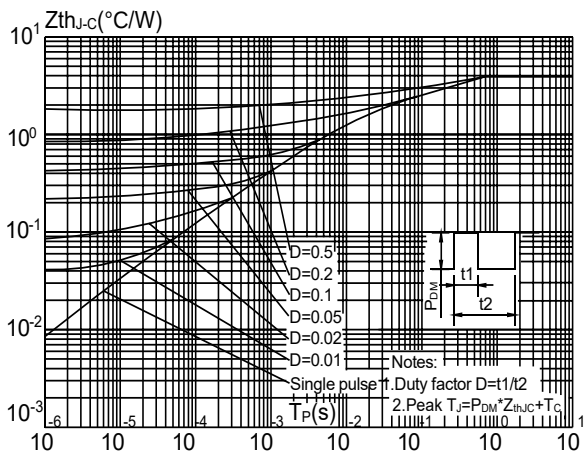


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case





Test Circuit-N

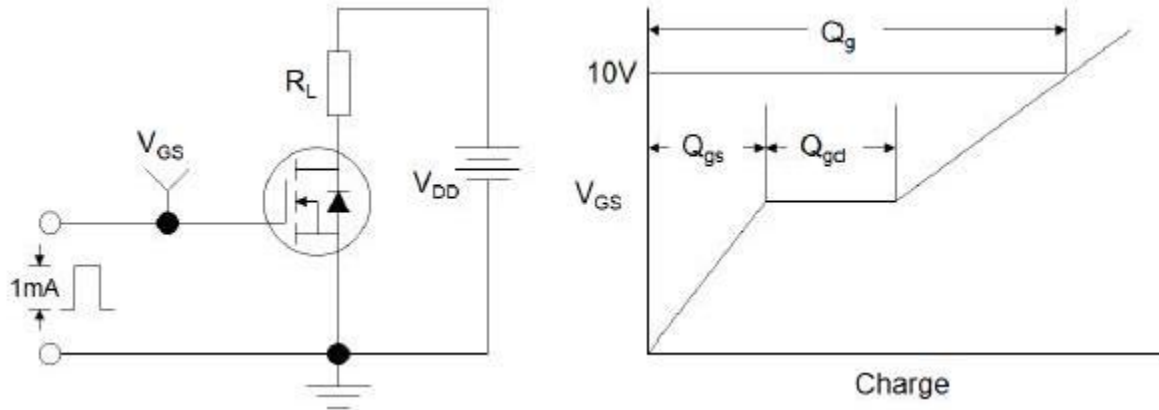


Figure1:Gate Charge Test Circuit & Waveform

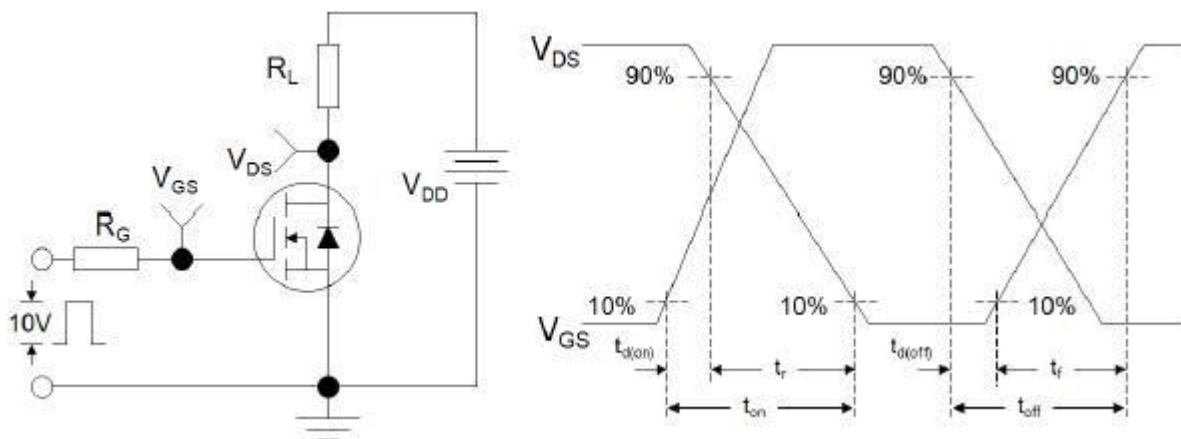


Figure 2: Resistive Switching Test Circuit & Waveforms

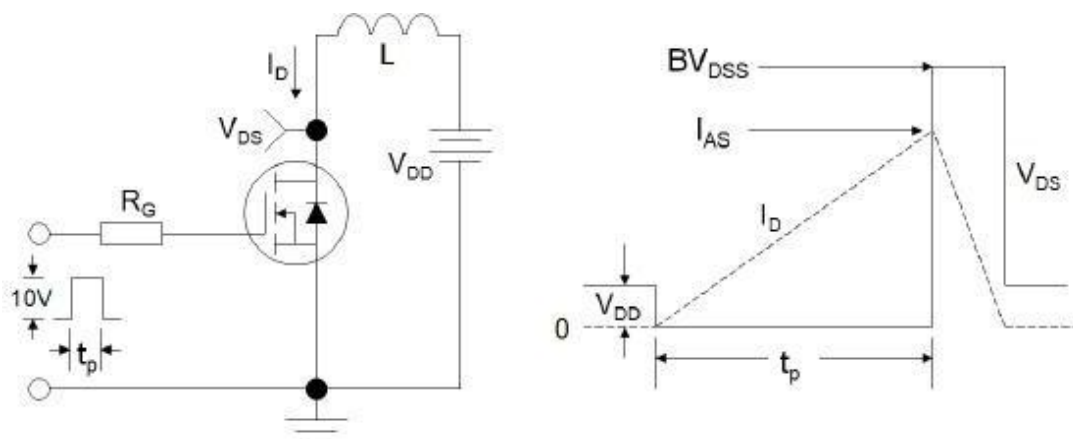


Figure 3:Unclamped Inductive Switching Test Circuit & Wavefor



P-Channel Typical Characteristics

Figure1: Output Characteristics

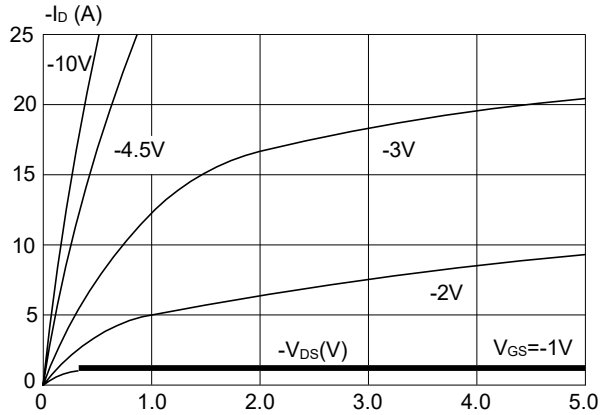


Figure 2: Typical Transfer Characteristics

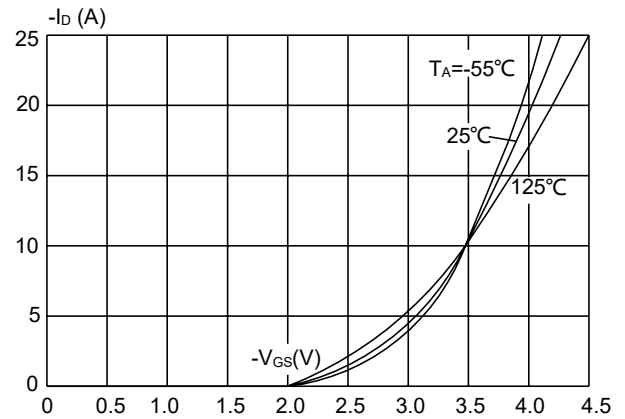


Figure 3: On-resistance vs. Drain Current

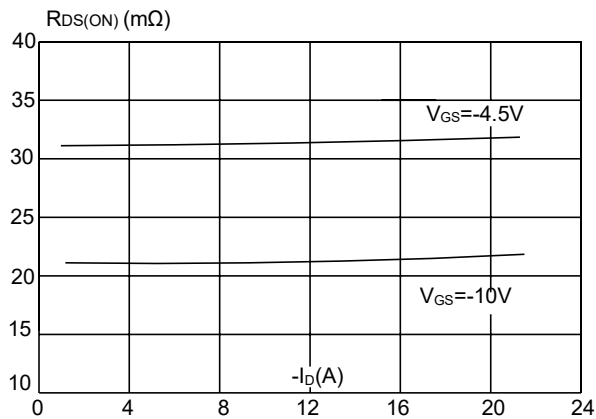


Figure 4: Body Diode Characteristics

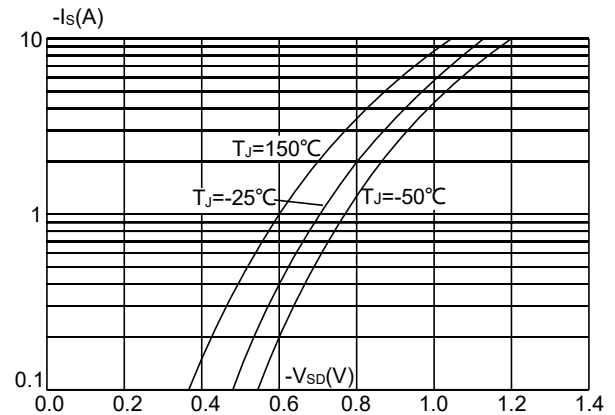


Figure 5: Gate Charge Characteristics

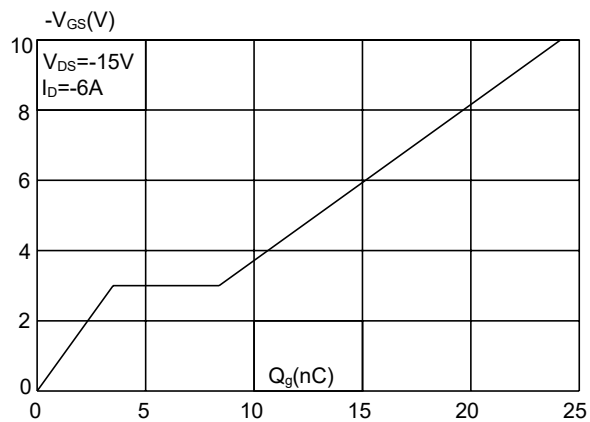


Figure 6: Capacitance Characteristics

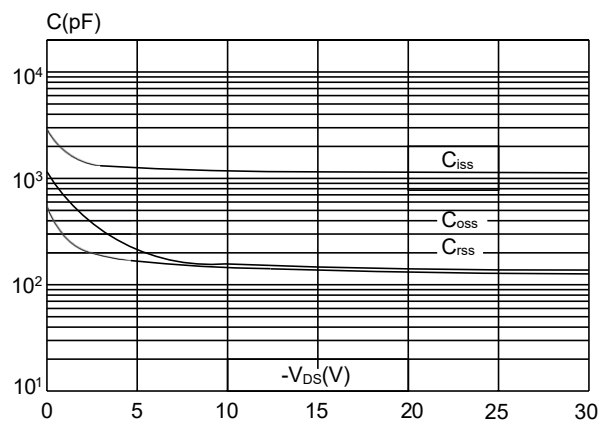




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

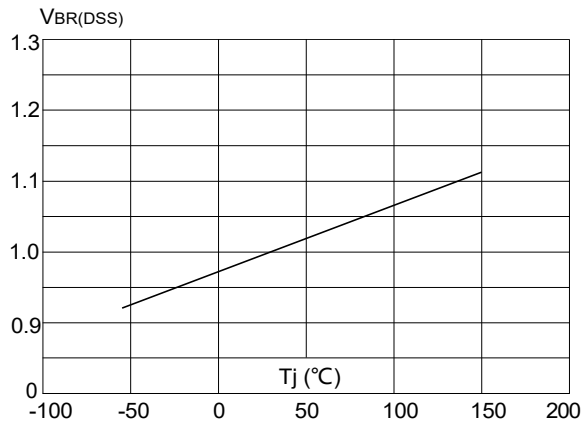


Figure 8: Normalized on Resistance vs. Junction Temperature

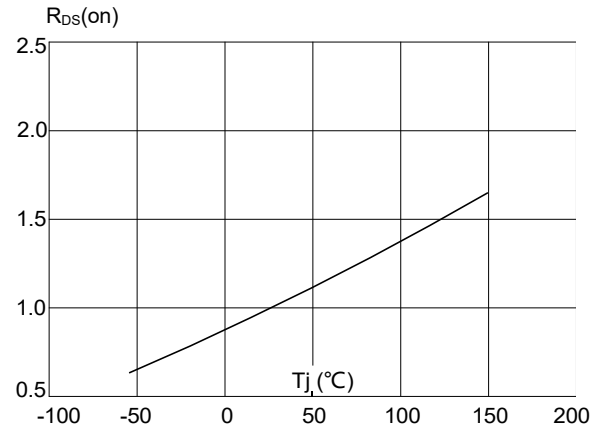


Figure 9: Maximum Safe Operating Area

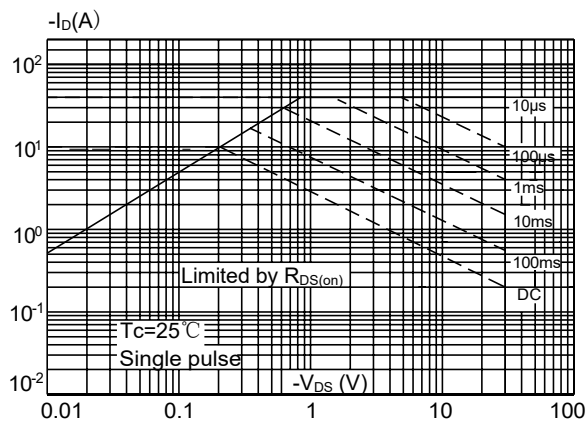


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

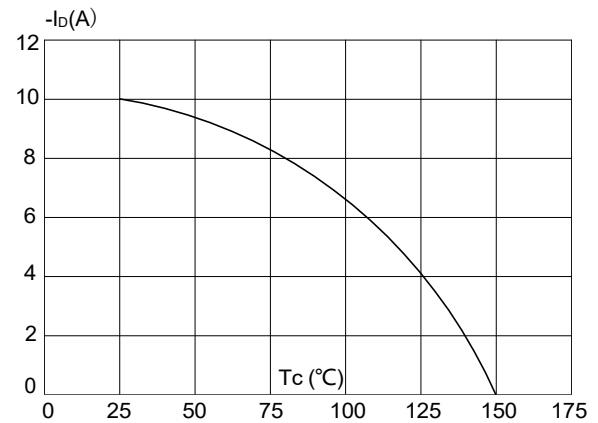
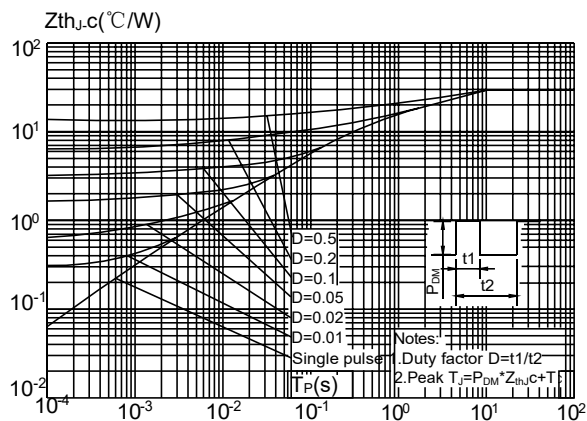


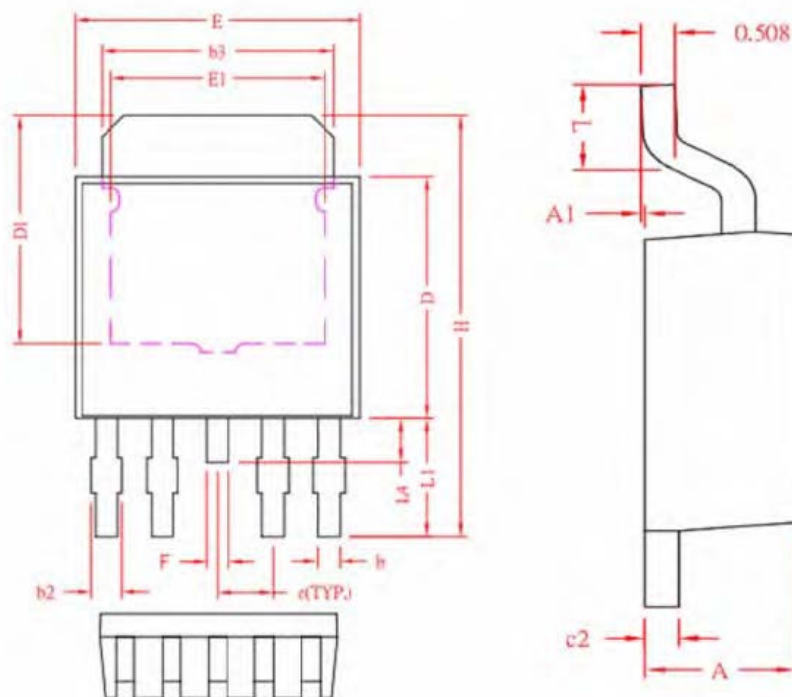
Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case







TO-252-4L Package Information



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	2.20	2.30	2.40
A1	0	0.08	0.15
b	0.45	0.53	0.60
b2	0.50	0.65	0.80
b3	5.20	5.35	5.50
c2	0.45	0.50	0.55
D	5.40	5.60	5.80
D1	4.57	-	-
E	6.40	6.60	6.80
E1	3.81	-	-
e	1.27 REF.		
F	0.40	0.50	0.60
H	9.40	9.80	10.20
L	1.40	1.59	1.77
L1	2.40	2.70	3.00
L4	0.80	1.00	1.20



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